

# MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

## MSN74LVC1G10DxxR

Product specification

## General Description

This single 3-input positive-NAND OR gate is designed for 1.65-V to 5.5-V VCC operation.

The MSN74LVC1G10DxxR device performs the Boolean function  $Y = \overline{A} \cdot \overline{B} \cdot \overline{C}$  or  $Y = \overline{A} + \overline{B} + \overline{C}$  in positive logic.

This device is fully specified for partial-power-down applications using Ioff. The Ioff circuitry disables the outputs, prevents damaging current backflow through the device when it is powered down.

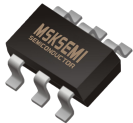
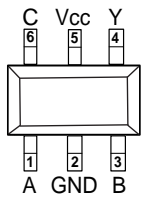


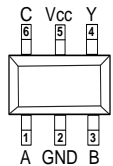

## Features

- Supports 5V Vcc operation
- Inputs accept voltages to 5.5 V
- Provides down translation to Vcc
- Low power consumption, 10-μA Max Icc
- ±24-mA output drive at 3.3 V
- Ioff supports live insertion, partial-power-down mode, and back drive protection

## Applications

- AV receivers
- DLP front projection system
- Digital picture frames
- Digital radio
- Digital still cameras
- Digital video cameras (DVC)
- GPS: personal navigation devices
- Handset: smartphones
- Notebook PC and netbooks
- Network-attached storage (NAS)
- Power line communication modems
- Server PSU
- STB, DVR, and streaming media

## Reference News

SOT-23-6	Pinning and Package	Marking	SC70-6	Pinning and Package	Marking
					

## Pin Functions

Pin		I/O	Description
Name	SOT23-6/SC70-6		
A	1	I	Data Input
GND	2	-	Ground
B	3	I	Data Input
Y	4	O	Data Output
VCC	5	-	Supply Voltage
C	6	I	Data Input

## Order information

Orderable Device	Package	Packing Option
MSN74LVC1G10DBVR	SOT23-6	3000PCS
MSN74LVC1G10DCKR	SC70-6	3000PCS

Absolute Maximum Ratings

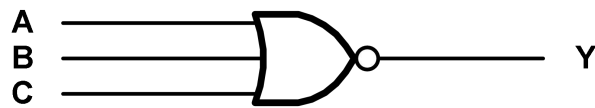
Parameters			Min	Max.	Unit
V <sub>CC</sub>	Supply voltage range		-0.5	6.5	V
V <sub>I</sub>	Input voltage range		-0.5	6.5	V
V <sub>O</sub>	Voltage range applied to any output in the high-impedance or power-off state <sup>(2)</sup>		-0.5	6.5	V
V <sub>O</sub>	Voltage range applied to any output in the high or low state <sup>(2)(3)</sup>		-0.5	V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> <0		-50	mA
I <sub>OK</sub>	Output clamp current	V <sub>O</sub> <0		-50	mA
I <sub>O</sub>	Continuous output current			±50	mA
Continuous current through V <sub>CC</sub> or GND				±100	mA
T <sub>J</sub>	Junction temperature under bias			85	°C
T <sub>stg</sub>	Storage temperature range		-65	150	°C

(1) Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

(3) The output positive-voltage rating may be exceeded up to 6.5 V maximum if the output current rating is observed

Functional Block Diagram



ESD Ratings

ESD			Value	Unit
V(ESD)	Electrostatic Discharge	Human-Body Model (HBM) <sup>(1)</sup>	8 K	V
		Charged-Device Model (CDM) <sup>(2)</sup>	2 K	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted)

Symbol	Parameter		Min	Max	Units
$V_{CC}$	Supply Voltage	Operating	1.65	5.5	V
$V_{IH}$	High-Level Input Voltage	$V_{CC}=1.65V$ to $1.95V$	$0.65 \times V_{CC}$		V
		$V_{CC}=2.3V$ to $2.7V$	1.7		
		$V_{CC}=3V$ to $3.6V$	2		
		$V_{CC}=4.5V$ to $5.5V$	$0.7 \times V_{CC}$		
$V_{IL}$	Low-Level Input Voltage	$V_{CC}=1.65V$ to $1.95V$		$0.35 \times V_{CC}$	V
		$V_{CC}=2.3V$ to $2.7V$		0.7	
		$V_{CC}=3V$ to $3.6V$		0.8	
		$V_{CC}=4.5V$ to $5.5V$		$0.3 \times V_{CC}$	
$V_I$	Input Voltage		0	5.5	V
$V_O$	Output Voltage		0	$V_{CC}$	V
$I_{OH}$	High-Level Output Current	$V_{CC}=1.65V$		-4	mA
		$V_{CC}=2.3V$		-8	
		$V_{CC}=3V$		-16	
				-24	
		$V_{CC}=4.5V$		-32	
$I_{OL}$	Low-Level Output Current	$V_{CC}=1.65V$		4	mA
		$V_{CC}=2.3V$		8	
		$V_{CC}=3V$		16	
				24	
		$V_{CC}=4.5V$		32	
$\Delta t/\Delta v$	Input Transition Rise or Fall Rate	$V_{CC}=1.8V \pm 0.15V, 2.5V \pm 0.2V$		20	ns/V
		$V_{CC}=3.3V \pm 0.3V$		10	
		$V_{CC}=5V \pm 0.5V$		5	
TA	Operating Free-air Temperature	All Other Packages	-40	125	°C

(1) All unused digital inputs of the device must be held at  $V_{CC}$  or GND to ensure proper device operation.

## Thermal Information

Package Type	$\theta_{JA}$	$\theta_{JC}$	Unit
SOT23-6	196	81	°C/W
SC70-6	178	98	°C/W

## Electrical Characteristics

Over recommended operating free-air temperature range (unless otherwise noted)

Parameter		Test Conditions	V <sub>CC</sub>	-40°C to 85°C			-40°C to 125°C			Unit
				Min	Typ	Max	Min	Typ	Max	
V <sub>OH</sub>		I <sub>OH</sub> =-100 μA	1.65 V to 5.5 V	V <sub>CC</sub> -0.1			V <sub>CC</sub> -0.1			V
		I <sub>OH</sub> =-4 mA	1.65 V	1.2			1.2			
		I <sub>OH</sub> =-8 mA	2.3 V	1.9			1.9			
		I <sub>OH</sub> =-16 mA	3 V	2.4			2.4			
		I <sub>OH</sub> =-24 mA		2.3			2.3			
		I <sub>OH</sub> =-32 mA	4.5 V	3.8			3.8			
V <sub>OL</sub>		I <sub>OL</sub> =100 μA	1.65 V to 5.5 V			0.1			0.1	V
		I <sub>OL</sub> =4 mA	1.65 V			0.45			0.45	
		I <sub>OL</sub> =8 mA	2.3 V			0.3			0.3	
		I <sub>OL</sub> =16 mA	3 V			0.4			0.4	
		I <sub>OL</sub> =24 mA				0.55			0.55	
		I <sub>OL</sub> =32 mA	4.5 V			0.55			0.55	
I <sub>I</sub>	A or B or C Inputs	V <sub>I</sub> =5.5 V or GND	0 to 5.5 V			±5			±5	μA
I <sub>ff</sub>		V <sub>I</sub> or V <sub>O</sub> =5.5 V	0			±10			±10	μA
I <sub>CC</sub>		V <sub>I</sub> =5.5 V or GND, I <sub>b</sub> =0	1.65 V to 5.5 V			10			10	μA
ΔI <sub>CC</sub>		One Input at V <sub>CC</sub> -0.6 V, Other Inputs at V <sub>CC</sub> or GND	3 V to 5.5 V			500			500	μA
C <sub>i</sub>		V <sub>I</sub> =V <sub>CC</sub> or GND	3.3 V		4			4		pF

(1) All unused digital inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation.

## Switching Characteristics, CL=15pF

Over recommended operating free-air temperature range (unless otherwise noted)

Parameter	From (Input)	To (Output)	-40°C to 85°C								Unit
			V <sub>CC</sub> =1.8 V ± 0.15 V		V <sub>CC</sub> =2.5 V ± 0.2 V		V <sub>CC</sub> =3.3 V ± 0.3 V		V <sub>CC</sub> =5 V ± 0.5 V		
			Min	Max	Min	Max	Min	Max	Min	Max	
tpd	A or B or C	Y	2.6	15.2	1.6	5.6	1.2	4.1	1	3.1	ns

Over recommended operating free-air temperature range, CL=30 pF or 50 pF (unless otherwise noted)

Parameter	From (Input)	To (Output)	-40°C to 85°C								Unit
			V <sub>CC</sub> =1.8 V ± 0.15 V		V <sub>CC</sub> =2.5 V ± 0.2 V		V <sub>CC</sub> =3.3 V ± 0.3 V		V <sub>CC</sub> =5 V ± 0.5 V		
			Min	Max	Min	Max	Min	Max	Min	Max	
tpd	A or B or C	Y	2.9	17.2	1.4	6.2	1.3	4.9	1	3.5	ns

Over recommended operating free-air temperature range, CL=30 pF or 50 pF (unless otherwise noted)

Parameter	From (Input)	To (Output)	-40°C to 125°C								Unit
			V <sub>CC</sub> =1.8 V ± 0.15 V		V <sub>CC</sub> =2.5 V ± 0.2 V		V <sub>CC</sub> =3.3 V ± 0.3 V		V <sub>CC</sub> =5 V ± 0.5 V		
			Min	Max	Min	Max	Min	Max	Min	Max	
tpd	A or B or C	Y	2.9	20	1.4	7.8	1.3	6.2	1	4.6	ns

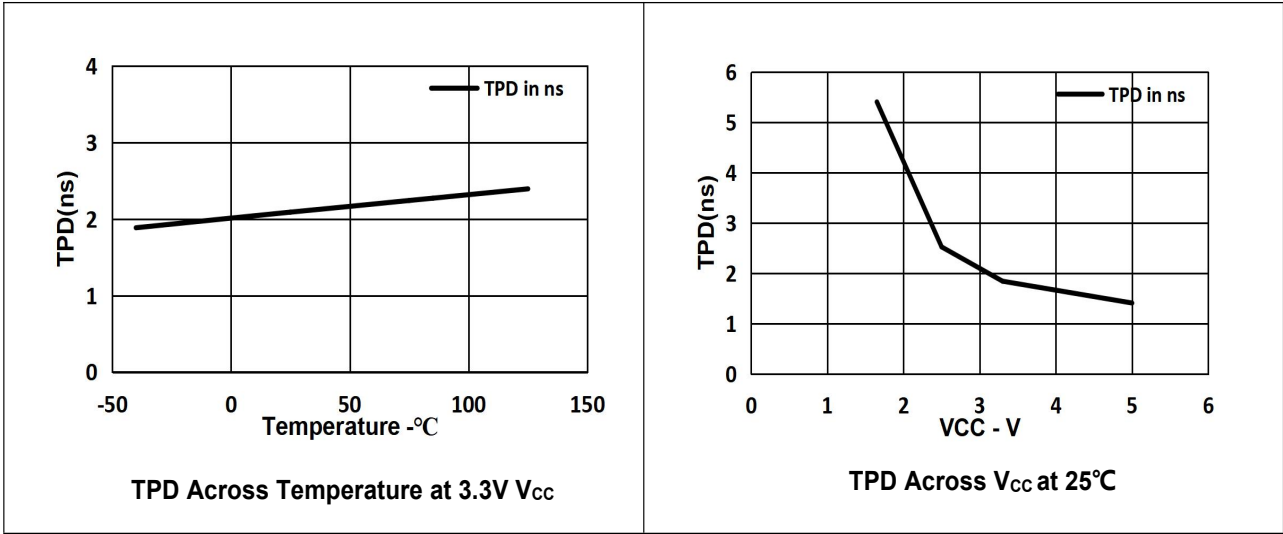
Operating Characteristics

TA=−40°C to +125°C

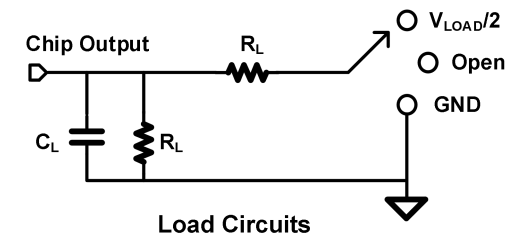
Parameter		Test Conditions	V <sub>CC</sub> =1.8V	V <sub>CC</sub> =2.5V	V <sub>CC</sub> =3.3V	V <sub>CC</sub> =5V	Units
			Typ	Typ	Typ	Typ	
C <sub>p</sub> d	Power Dissipation Capacitance	f=10Mhz	18	19	20	23	pF

Typical Characteristics

V<sub>CC</sub>=1.65V or 5.5V, FULL=−40°C to +125°C. Typical values are at TA=+25°C (unless otherwise noted)



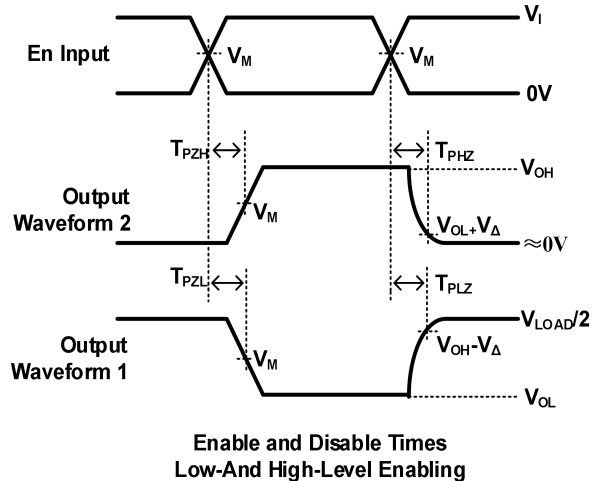
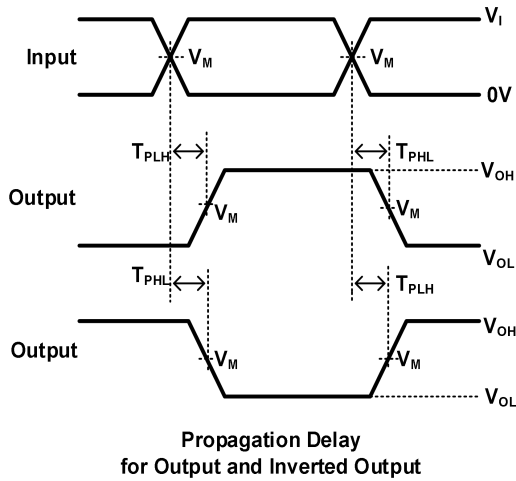
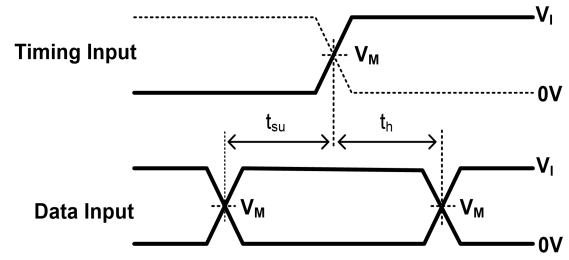
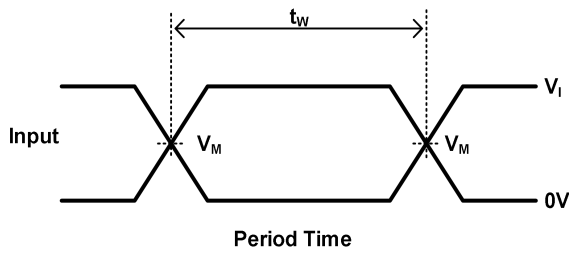
Parameter Measurement Information



TEST	S1
T <sub>PHL</sub> /T <sub>PLH</sub>	OPEN
T <sub>PLZ</sub> /T <sub>PZL</sub>	V <sub>LOAD</sub>
T <sub>PHZ</sub> /T <sub>PZH</sub>	GND

V <sub>CC</sub>	INPUTS		V <sub>M</sub>	V <sub>LOAD</sub>	C <sub>L</sub>	R <sub>L</sub>	V <sub>Δ</sub>
	V <sub>I</sub>	T <sub>r</sub> /T <sub>f</sub>					
1.8V±0.15V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	2×V <sub>CC</sub>	15pF	1MΩ	0.15V
2.5V±0.15V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	2×V <sub>CC</sub>	15pF	1MΩ	0.15V
3.3V±0.15V	3V	≤2.5ns	1.5V	6V	15pF	1MΩ	0.3V
5V±0.15V	V <sub>CC</sub>	≤2.5ns	V <sub>CC</sub> /2	2×V <sub>CC</sub>	15pF	1MΩ	0.3V

## Parameter Measurement Information(Continued)



Notes: A.  $C_L$  includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.

C. All input pulses are supplied by generators having the following characteristics: PRR 10 MHz,  $Z = 50$ .

D. The outputs are measured one at a time, with one transition per measurement.

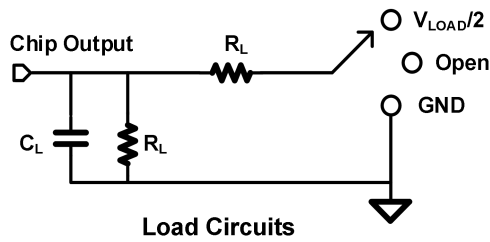
E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .

F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .

G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

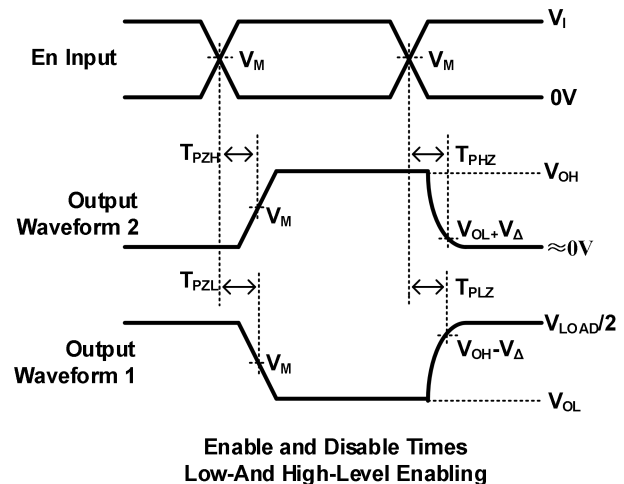
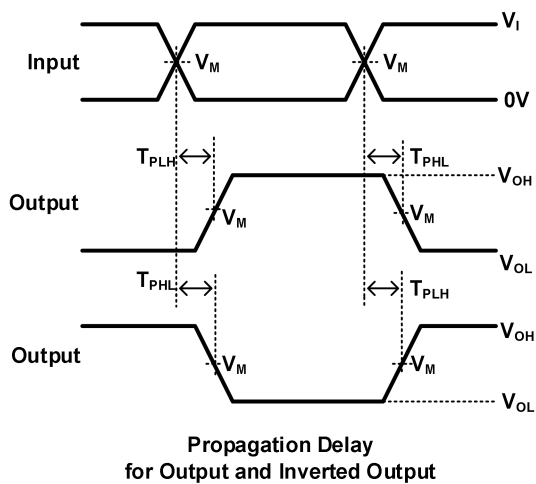
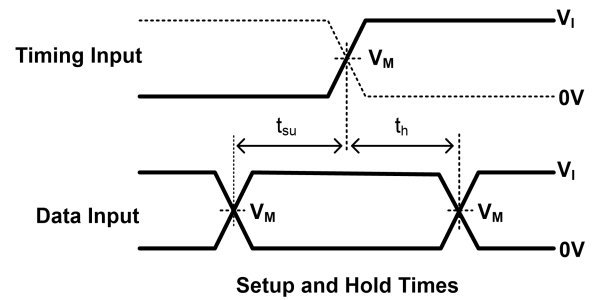
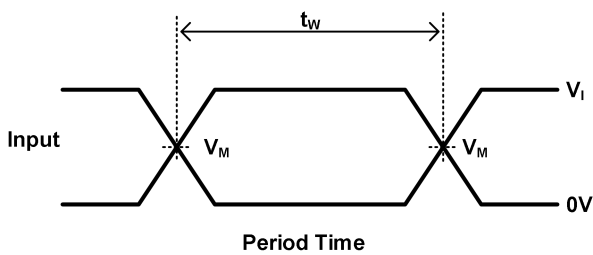
H. All parameters and waveforms are not applicable to all devices.

## Parameter Measurement Information(Continued)



TEST	S1
$T_{PHL}/T_{PLH}$	OPEN
$T_{PLZ}/T_{PZL}$	$V_{LOAD}$
$T_{PHZ}/T_{PZH}$	GND

$V_{CC}$	INPUTS		$V_M$	$V_{LOAD}$	$C_L$	$R_L$	$V_{\Delta}$
	$V_I$	$T_r/T_f$					
$1.8V \pm 0.15V$	$V_{CC}$	$\leq 2ns$	$V_{CC}/2$	$2 \times V_{CC}$	30pF	1k $\Omega$	0.15V
$2.5V \pm 0.15V$	$V_{CC}$	$\leq 2ns$	$V_{CC}/2$	$2 \times V_{CC}$	30pF	500 $\Omega$	0.15V
$3.3V \pm 0.15V$	3V	$\leq 2.5ns$	1.5V	6V	50pF	500 $\Omega$	0.3V
$5V \pm 0.15V$	$V_{CC}$	$\leq 2.5ns$	$V_{CC}/2$	$2 \times V_{CC}$	50pF	500 $\Omega$	0.3V



Notes: A. C includes probe and jig capacitance.

B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.

C. All input pulses are supplied by generators having the following characteristics: PRR 10 MHz, Z=50.

D. The outputs are measured one at a time, with one transition per measurement.

E.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis}$ .

F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .

G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .

H. All parameters and waveforms are not applicable to all device.



Detailed Description

This 3-input NAND gate is designed for 1.65-V to 5.5-V  $V_{CC}$  operation. The MSN74LVC1G10DxxR device features a three-input NAND gate. The output state is determined by eight patterns of 3-bit input. All inputs can be connected to  $V_{CC}$  or GND. This device is fully specified for partial-power-down applications using  $I_{off}$ . The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

Feature Description

- Wide operating voltage range.
- Operates from 1.65 V to 5.5 V.
- Allows down voltage translation.
- Inputs accept voltages to 5.5 V.
- $I_{off}$  feature allows voltages on the inputs and outputs, when  $V_{CC}$  is 0 V.

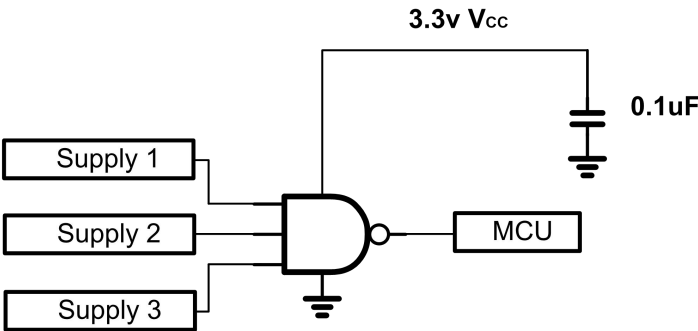
Device Functional Modes

Input A			Output
A	B	C	Y
H	H	H	L
L	X	X	H
X	L	X	H
X	X	L	H

Application Information

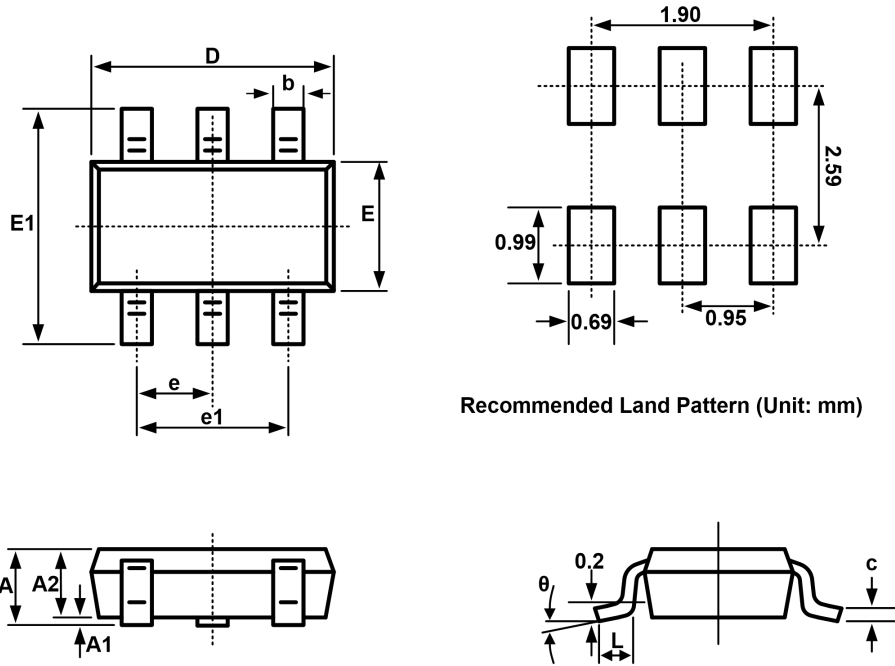
The MSN74LVC1G10DxxR device offers logical NAND configuration for many design applications. This example describes basic power sequencing using the NAND gate configuration. Power sequencing is often used in applications that require a processor or other delicate device with specific voltage timing requirements in order to protect the device from malfunctioning. In the application below, the power-good signals from the supplies tell the MCU to continue an operation.

Typical Application



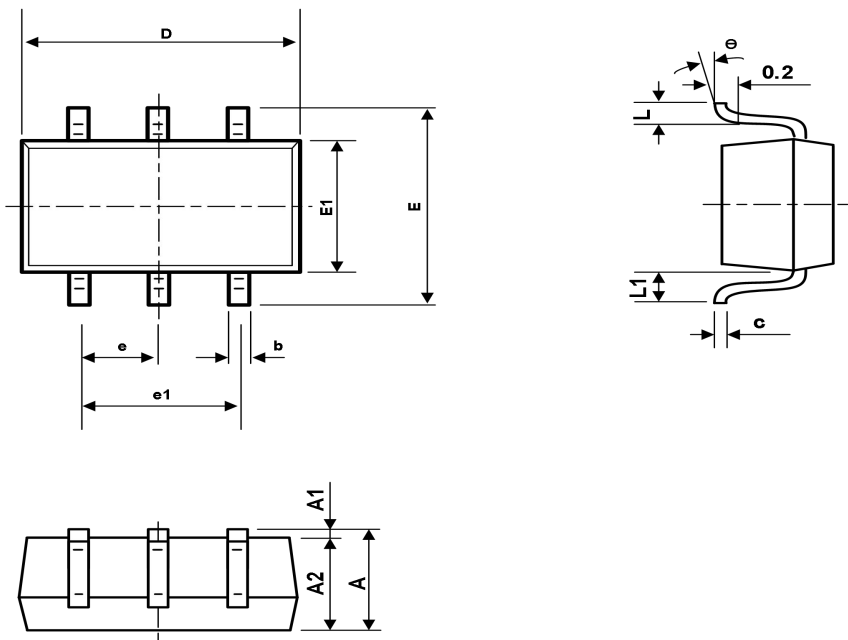
Typical Application Diagram

Package Outline  
SOT23-6



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950BSC		0.037BSC	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
L1	0.600REF		0.024REF	
θ	0°	8°	0°	8°

**Package Outline**  
**SC70-6**



Symbol	Dimension In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.	1.	0.	0.
A1	9000.	1000.	0350.	0430.
A2	0000.	1001.	0000.	0040.
b	9000.	0000.	0350.	0390.
c	1500.	3500.	0060.	0140.
D	1102.	1752.	0040.	0070.
E	0002.	2002.	0790.	0870.
E1	1501.	4501.	0850.	0960.
e	0.650TYP		0.026TYP	
e1	1501.	3501.	0450.	0530.
L	2000.	4000.	0470.	0550.
L1	260	0.525REF 460	010	0.021REF 018
θ	0°	8°	0°	8°

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